Signetics

SCN8032AH/SCN8052AH Single-Chip 8-Bit Microcontroller

Product Specification

Microprocessor Division

DESCRIPTION

The Signetics SCN8032AH/SCN8052AH is a high-performance microcontroller fabricated using the Signetics highly reliable +5V, depletion-load, N-channel, silicon-gate, N500 MOS process technology. It provides the hardware features, architectural enhancements and instructions that are necessary to make it a powerful and cost-effective controller for applications requiring up to 64K bytes of programming memory and up to 64K bytes of data storage.

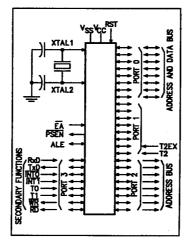
The SCN8032AH contains 256 bytes of read/write data memory, 32 1/O lines configured as four 8-bit ports, three 16-bit timer/counters, a six-source two-priority-level nested interrupt structure, a programmable serial 1/O port and an on-chip oscillator and clock circuitry. The SCN8052AH has all of these features plus 8K bytes of non-volatile read-only program memory. Both microcontrollers have memory expansion capabilities of up to 64K bytes of data storage and 64K bytes of program memory that may be realized with standard TTL compatible memories.

Because of its extensive BCD/binary arithmetic and bit-handling facilities, the SCN8032AH/SCN8052AH microcontroller is efficient at both computational and control-oriented tasks. Efficient use of program memory is also achieved by using the familiar compact instruction set of the 8031/8051. Forty-four percent of the instructions are one-byte, 41% two-byte, and 15% three-byte instructions. With a 12MHz crystal, the majority of the instructions execute in just 1.0µs. The longest instructions, multiply and divide, require only 4µs at 12MHz.

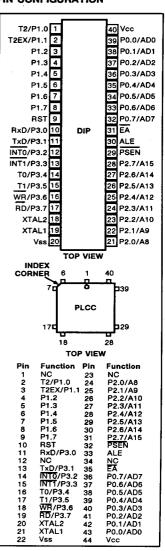
FEATURES

- SCN8032AH control-oriented CPU with RAM and I/O
- SCN8052AH an SCN8032AH with factory mask-programmable ROM
- 8K X 8 ROM (SCN8052AH only)
- 256 X 8 RAM
- 32 I/O lines (four 8-bit ports)
- Three 16-bit timer/counters
- Programmable full-duplex serial channel
 - Variable transmit/receive baud rate capability
- Timer 2 capture capability
- External memory addressing
- 64K ROM and 64K RAM
- Boolean processor
- 128 user bit-addressable locations
- Upward compatible with SCN8031AH/SCN8051AH

LOGIC SYMBOL



PIN CONFIGURATION

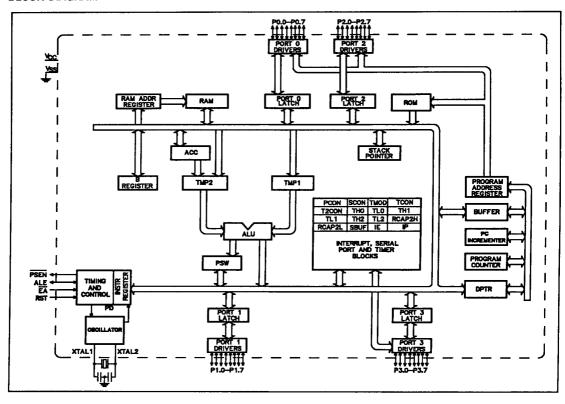


SCN8032AH/SCN8052AH

ORDERING INFORMATION SCN80 DDHDDDDD (CPxxxx) ROM/RAM (bytes) Custom ROM Pattern No. 32 = Ext/256 52 = 8K/256 Applies to masked ROM versions only. Number will be assigned by Signetics. Contact Signetics sales office for ROM pattern submission requirements. Consumption H - Reduced Power AH 40 = 40-pin 44 = 44-pin Package A - Plastic LCC I - Ceramic DIP N = Plastic DIP C = 3.5 to 12MHz F = 3.5 to 15MHz Operating Temperature Range A = -40 °C to +85 °C C = 0 °C to +70 °C

PART NUMBER SELECTION					
ROMIess	ROM	Temperature and Package	Frequency		
SCN8032HCCN40	SCN8052HCCN40	0 to +70°C, plastic DIP	3.5 to 12MHz		
SCN8032HCCA44	SCN8052HCCA44	0 to +70°C, plastic LCC	3.5 to 12MHz		
SCN8032HACN40	SCN8052HACN40	-40 to +85°C, plastic DIP	3.5 to 12MHz		
SCN8032HACA44	SCN8052HACA44	-40 to +85°C, plastic LCC	3.5 to 12MHz		
SCN8032HCFN40	SCN8052HCFN40	0 to +70°C, plastic DIP	3.5 to 15MHz		
SCN8032HCFA44	SCN8052HCFA44	0 to +70°C, plastic PLCC	3.5 to 15MHz		
SCN8032HAFN40	SCN8052HAFN40	-40 to +85°C, plastic DIP	3.5 to 15MHz		
SCN8032HAFA44	SCN8052HAFA44	-40 to +85°C, plastic PLCC	3.5 to 15MHz		

BLOCK DIAGRAM



SCN8032AH/SCN8052AH

PIN DESCRIPTION

	PIN	NO.		NAME AND FUNCTION
MNEMONIC	DIP	LCC	TYPE	NAME AND FONCTION
V _{SS}	20	22	ı	Ground: 0V reference.
Vcc	40	44	1	Power Supply: This is the power supply voltage for normal operation.
P0.0-P0.7	39-32	43-36	1/0	Port 0: Port 0 is an open-drain, bidirectional I/O port. Port 0 is also the multiplexed low-order address and data bus during accesses to external program and data memory. In this application, it uses strong internal pullups when emitting 1s. Port 0 also outputs the code bytes during program verification.
P1.0-P1.7	1-8	2-9	1/0	Port 1: Port 1 is an 8-bit bidirectional I/O port with internal pull-ups. Pins P1.0 and P1.1 also correspond to the special functions T2, timer 2 counter trigger input, and T2EX, external input to timer 2. The output latch on these two special functions must be programmed to one for that function to operate. Port 1 also receives the low-order address byte during program verification.
	1 2	2 3	l I	T2 (P1.0): Timer/counter 2 trigger input. T2EX (P1.1): Timer/counter 2 external count input.
P2.0-P2.7	21-28	24-31	1/0	Port 2: Port 2 is an 8-bit bidirectional I/O port with internal pull-ups. Port 2 emits the high-order address byte during fetches from external program memory and during accesses to external data memory that use 16-bit addresses (MOVX @DPTR). During accesses to external data memory that use 8-bit addresses (MOVX @Ri), port 2 emits the contents of the P2 special function register.
P3.0-P3.7	10–17	11, 13–19	1/0	Port 3: Port 3 is an 8-bit bidirectional I/O port with internal pullups. Port 3 is also used for the special features listed below:
	10 11 12 13 14 15 16	11 13 14 15 16 17 18	1 0 1 1 0 0	RxD (P3.0): Serial input port TxD (P3.1): Serial output port INTO (P3.2): External interrupt INT1 (P3.3): External interrupt T0 (P3.4): Timer 0 external input T1 (P3.5): Timer 1 external input WR (P3.6): External data memory write strobe RD (P3.7): External data memory read strobe
RST	9	10	l	Reset: A high on this pin for two machine cycles while the oscillator is running, resets the device. A small external pull-down resistor (\cong 8.2K Ω) from RST to V _{SS} permits power-on reset when a capacitor (\cong 10 μ f) is also connected from this pin to V _{CC} .
ALE	30	33	1/0	Address Latch Enable: Output pulse for latching the low byte of the address during an access to external memory. In normal operation, ALE is emitted at a constant rate of 1/6 the oscillator frequency, and can be used for external timing or clocking. Note that one ALE pulse is skipped during each access to external data memory.
PSEN	29	32	0	Program Store Enable: The read strobe to external program memory. When the device is executing code from external program memory, PSEN is activated twice each machine cycle, except that two PSEN activations are skipped during each access to external data memory. PSEN is not activated during fetches from internal program memory.
ĒĀ	31	35	1	External Access Enable: EA must be externally held low to enable the device to fetch code from external program memory locations 0000H and 1FFFH. If EA is held high, the device executes from internal program memory unless the program counter contains an address greater than 1FFFH.
XTAL1	19	21	1	Crystal 1: Input to the inverting oscillator amplifier and input to the internal clock generator circuits.
XTAL2	18	20	0	Crystal 2: Output from the inverting oscillator amplifier.

SCN8032AH/SCN8052AH

OSCILLATOR CHARACTERISTICS

XTAL1 and XTAL2 are the input and output, respectively, of an inverting amplifier. The pins can be configured for use as an on-chip oscillator, as shown in the logic symbol, page 1.

To drive the device from an external clock source, XTAL2 should be driven while XTAL1 should be grounded. There are no requirements on the duty cycle of the external clock signal, because the input to the internal clock circuitry is through a divide-by-two flip-flop. However, minimum and maximum high and low times specified in the data sheet must be observed.

RESET

A reset is accomplished by holding the RST pin high for at least two machine cycles (24 oscillator periods), while the oscillator is running.

ABSOLUTE MAXIMUM RATINGS1, 2, 3

PARAMETER	RATING	UNIT
Storage temperature range	-65 to +150	°C
All voltages with respect to ground	-0.5 to +7.0	V
Power dissipation	2.0	w

DC ELECTRICAL CHARACTERISTICS TA - 0°C to +70°C , VCC - 5V ±10%, VSS - 0V4, 5

Symbol	Parameter	Test Conditions	Li		
	, aramotor	rest Conditions	Min	Max	Unit
VIL	Input low voltage		-0.5	0.8	V
V _{IH}	Input high voltage, except RST and XTAL2		2	V _{CC} +0.5	V
V _{IH1}	Input high voltage to RST for reset, XTAL2	XTAL1 to V _{SS}	2.5	V _{CC} +0.5	V
v_{OL}	Output low voltage, ports 1, 2, 36	I _{OL} = 1.6mA		0.45	٧
V _{OL1}	Output low voltage, port 0, ALE, PSEN6	I _{OL} = 3.2mA		0.45	V
V _{OH}	Output high voltage, ports 1, 2, 3	I _{OH} = -80µA	2.4		V
V _{OH1}	Output high voltage port 0 in external bus mode, ALE, PSEN)3	I _{OH} = -400µA	2.4		٧
I _{IL}	Logical 0 input current, ports 1, 2, 3	V _{IN} = 0.45V		-800	μА
l _{IH1}	Input high curent to RST for reset	V _{IN} = V _{CC} - 1.5V		500	μА
Li	Input leakage current, port 0, EA	0.45 < V _{IN} < V _{CC}		±10	μA
IL2	Logical 0 input current for XTAL2	XTAL1 = V _{SS} , V _{IN} = 0.45V		-3.2	mA
cc	Power supply current	All outputs disconnected and EA = V _{CC}		175	mA
Cio	Pin capacitance	f _C = 1MHz, T _A = 25°C		10	pF

$T_A = -40^{\circ}C$ to $+85^{\circ}C$ - Extended temperature range - SCN8052HAC only

VIH	Input high voltage, except RST and XTAL2		2.2	V _{CC} +0.5	V
V _{IH1}	Input high voltage to RST for reset, XTAL2	XTAL1 to V _{SS}	2.7		v
lcc	Power supply current	All outputs disconnected and EA = V _{CC}		175	mA

NOTES:

- Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any conditions other than those described in the AC and DC Electrical Characteristics section of this specification is not implied.
- 2 For operating at elevated temperatures, the device must be derated based on +150°C maximum junction temperature.
- 3. This product includes circuitry specifically designed for the protection of its internal devices from the damaging effects of excessive static charge. Nonetheless, it is suggested that conventional precautions be taken to avoid applying voltages greater than the rated maxima.
 Parameters are valid over operating temperature range unless otherwise excessive.
- charge. Nonetheless, it is suggested that conventional precautions be taxen to avoid applying voltages greater than the rates invalid.

 b. Parameters are valid over operating temperature range unless otherwise specified.

 All voltage measurements are referenced to ground. For testing, all input signals swing between 0.45V and 2.4V with a transition time of 20ns maximum. All time measurements are referenced at input voltages of 0.8V and 2.0V and at output voltages of 0.8V and 2.0V as
- VOL is degraded when the device rapidly discharges external capacitance. This AC noise is most pronounced during emission of address data. When using external memory, locate the latch or buffer as close to the device as possible.
 Emitting Degraded

February 1989

SCN8032AH/SCN8052AH

AC ELECTRICAL CHARACTERISTICS TA = 0°C to +70°C or -40°C to +85°C, V_{CC} = 5V ±10%, V_{SS} = 0V¹, 2

			12MHz CLOCK		VARIABLE CLOCK		
SYMBOL	FIGURE	PARAMETER	Min	Max	Min	Max	UNI
Program	Memory				T		
1/t _{CLCL}		Oscillator frequency: Speed Versions SCN8052 C			3.5	12	мн
		SCN8052 C SCN8052 F			3.5	15	мн
•	1	ALE pulse width	127		2t _{CLCL} -40		ns
t _{LHLL} t _{AVLL}	1	Address valid to ALE low	43		t _{CLCL} -40		ns
tLLAX	1	Address hold after ALE low	48		t _{CLCL} -35		ns
tLLIV	1-1-	ALE low to valid instruction in		233		4t _{CLCL} -100	n
	1	ALE low to PSEN low	58		t _{CLCL} -25		n:
t _{LLPL}	1	PSEN pulse width	215		3t _{CLCL} -35		n:
t _{PLPH}	1	PSEN low to valid instruction in		125		3t _{CLCL} -125	n:
t _{PLIV}	1	Input instruction hold after PSEN	0		0		n
t _{PXIX}	1	Input instruction float after PSEN		63		t _{CLCL} -20	n
t _{PXIZ}	1	Address to valid instruction in		302		5t _{CLCL} -115	n
	1	PSEN low to address float		20		20	n
t _{PLAZ}	1	PSEN to address valid	75		t _{CLCL} -8		n
t _{PXAV} Data Me		PSEN (O address valid					_
t _{RLBH}	2	RD pulse width	400		6t _{CLCL} -100		n
twrm.	3	WR pulse width	400		6t _{CLCL} -100		n
	2	RD low to valid data in		252		5t _{CLCL} -165	n
†RLDV	2	Data hold after RD	0		0		n
trhox	2	Data float after RD		97		2t _{CLCL} -70	n
tri SV	2	ALE low to valid data in		517		8t _{CLCL} -150	n
t _{LLDV}	2	Address to valid data in		585		9t _{CLCL} -165	n
	2, 3	ALE low to RD or WR low	200	300	3t _{CLCL} -50	3t _{CLCL} +50	n
tulwl	2, 3	Address valid to WR low or RD low	203		4t _{CLCL} -130		n
t _{AVWL}	3	Data valid to WR transition	23		t _{CLCL} -60		n
t _{QVWX}	3	Data vaid to WR high	433		7t _{CLCL} -150		n
tovwh	3	Data hold after WR	33		t _{CLCL} -8		n
twHQX_	2	RD low to address float		-20	1	20	n
t _{RLAZ}	2, 3	RD or WR high to ALE high	43	123	t _{CLCL} -40	t _{CLCL} +40	n
twhLH External		AD OF WA High to ALL High	1				
tchcx	5	High time			20		n
tolox	5	Low time			20		n
tCLCH	5	Rise time				20	n
tCHCL	5	Fall time				20	n
Shift Reg	ister						
txLXL	4	Serial port clock cycle time	1.0		12t _{CLCL}		<u> </u>
tavxH	4	Output data setup to clock rising edge	700	ļ	10t _{CLCL} -133		n
txHQX	4	Output data hold after clock rising edge	50		2t _{CLCL} -117		n
^t XHDX	4	Input data hold after clock rising edge	0	1 705	0	404 400	n
tXHDV	4	Clock rising edge to input data valid		700		10t _{CLCL} -133	n

NOTES:

1. Parameters are valid over operating temperature range unless otherwise specified.

2. Load capacitance for port 0, ALE, and PSEN = 100pF, load capacitance for all other outputs = 80pF.

EXPLANATION OF THE AC SYMBOLS

Each timing symbol has five characters. The first character is always 't' (- time). The other characters, depending on their positions, indicate the name of a signal or the logical status of that signal. The designations are:

A - Address

C - Clock

D - Input data

H - Logic level high

1 - Instruction (program memory contents)

L - Logic level low, or ALE

P- PSEN

Q - Output data

R - RD signal

t - Time

V - Valid

W - WR signal X - No longer a valid logic level

Z - Float

Examples: tAVLL - Time for address valid to ALE low.

tLLPL - Time for ALE low to PSEN low.

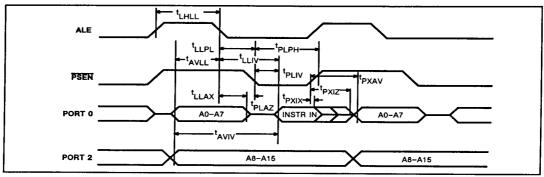


Figure 1. External Program Memory Read Cycle

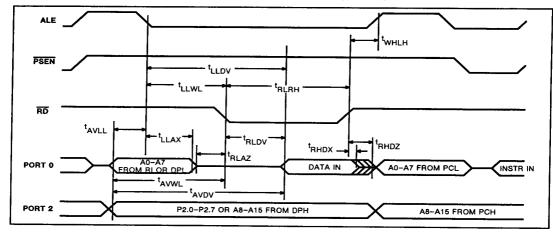


Figure 2. External Data Memory Read Cycle

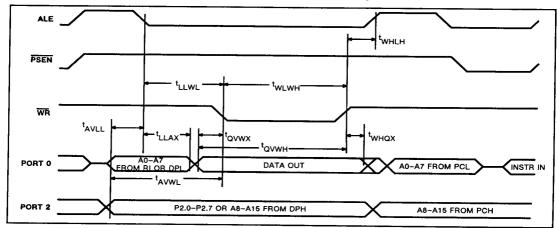


Figure 3. External Data Memory Write Cycle

February 1989

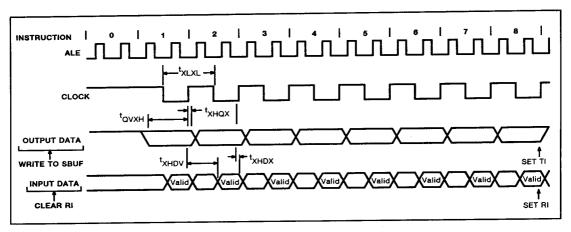


Figure 4. Shift Register Mode Timing

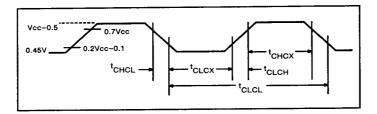


Figure 5. External Clock Drive

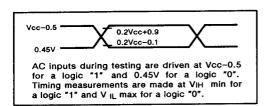
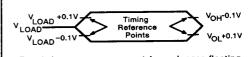


Figure 6. AC Testing Input/Output



For timing purposes, a port is no longer floating when a 100mV change from load voltage occurs, and begins to float when a 100mV change from the loaded V_{OH}/VoL level occurs. loH/loL≥±20mA.

Figure 7. Float Waveform